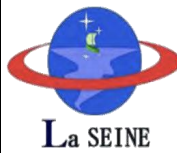




The 6th

# Mission Idea Contest

For Achieving Sustainable Development Goals with Human Spaceflight



## *On-orbit Measurements of Radiation Effects on Commercial-Off-The-Shelf (COTS) Hardware for Small Satellites*

---

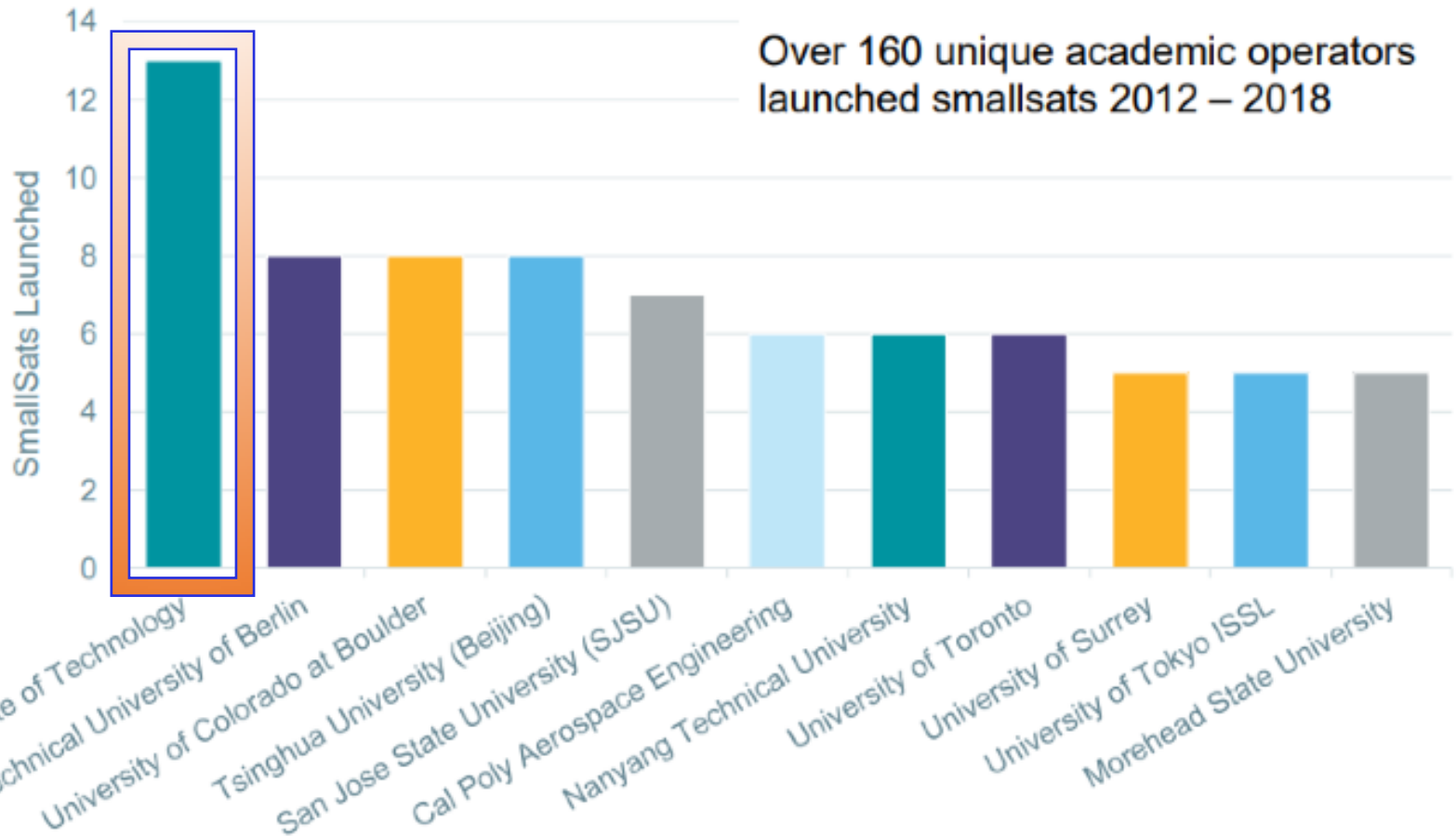
**Senior Shimhanda and Tomoaki Murase**

**Laboratory of Spacecraft Environment Interactions Engineering**



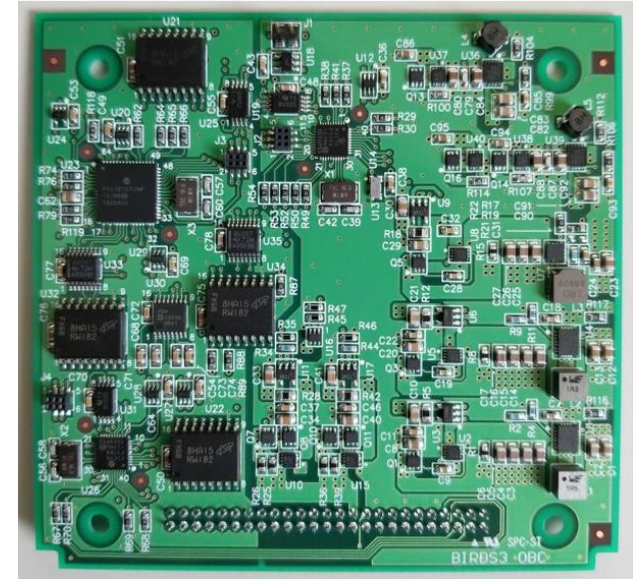
# Introduction (1/5)

## Academic Operators with 5+ Smallsats Deployed



# Introduction (2/5)

- ❑ We use **COTS components** in most subsystems.
- ❑ Why COTS?
  - Low cost
  - Fast delivery
- ❑ Demerits
  - High **risk** approach
  - Not space-proven/**radiation-hardened**



© Kyutech



CPU(PIC)



MOSFET

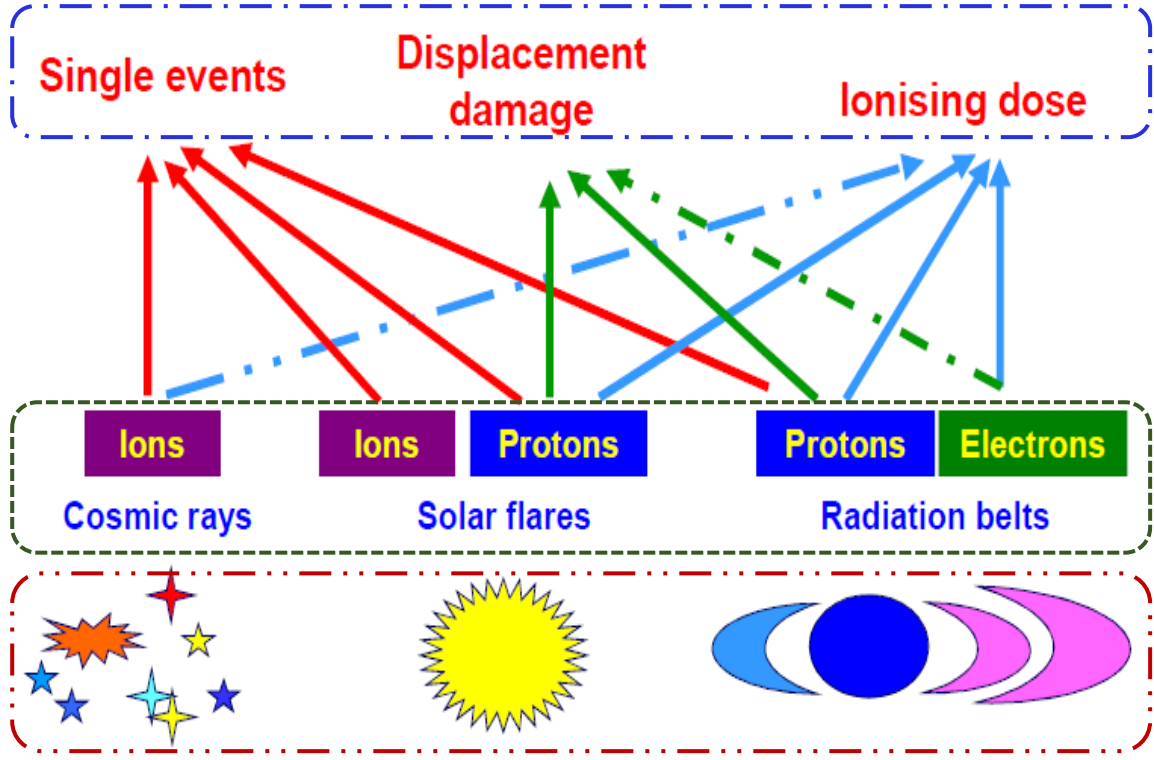
# Introduction (3/5)

## Effect of radiation on electronic devices

• effects

• particles

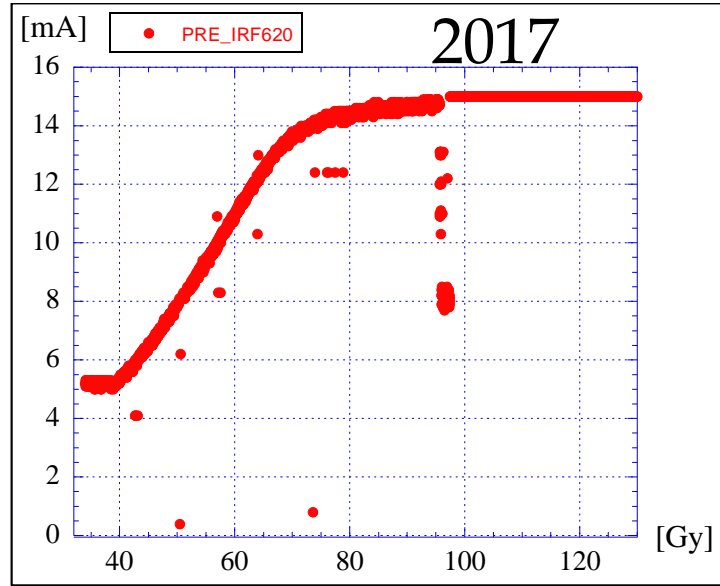
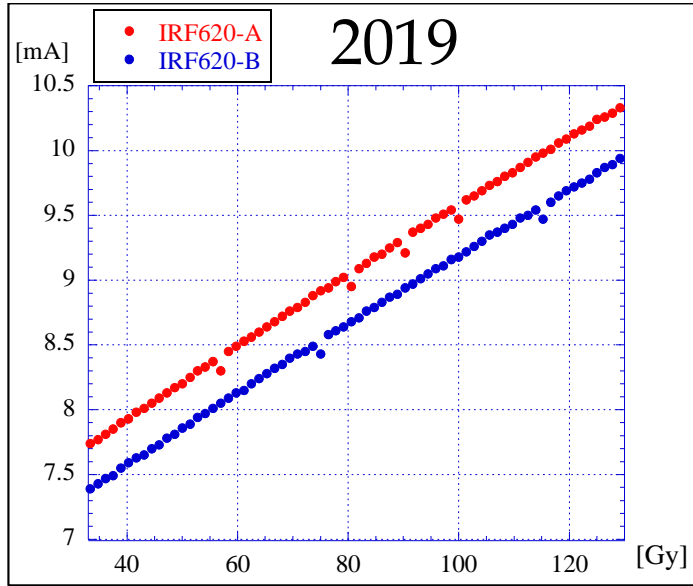
• sources



# Introduction (4/5)

To manage the **risk**, we irradiate COTS components

Present results



Next step

Implementation of **irradiation** of COTS components onboard **ISS** under **actual space conditions** from the **viewpoint** of checking the **accuracy** of ground test



# Introduction (5/5)

## Consumer parts database on micro satellite

Citizenship Satellite Initiative for Connected Industries

Satellite list

About the database

New registration application

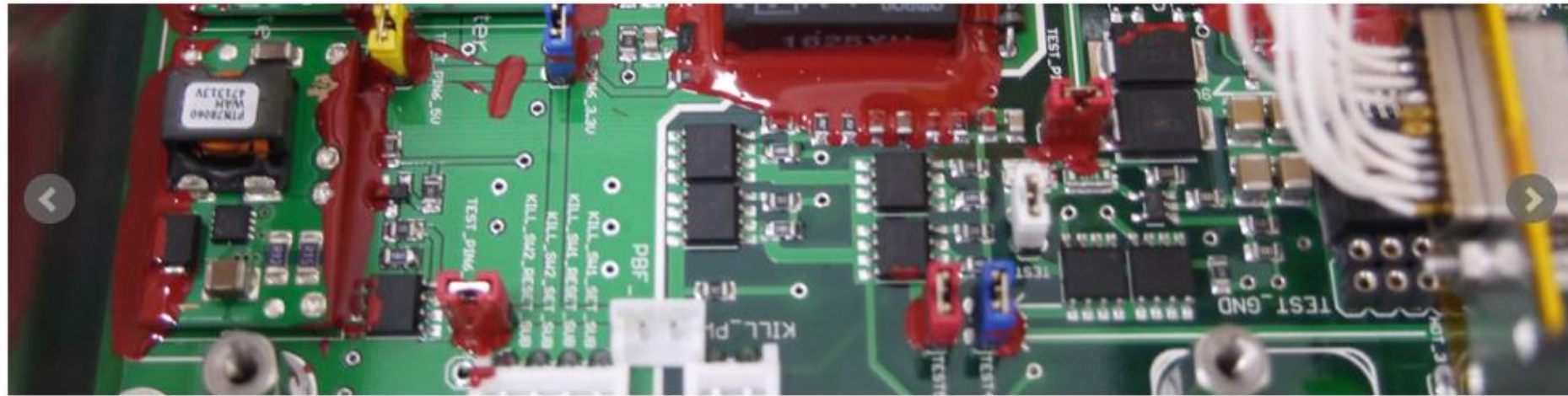
Search page

How to import CSV data

Contact Us

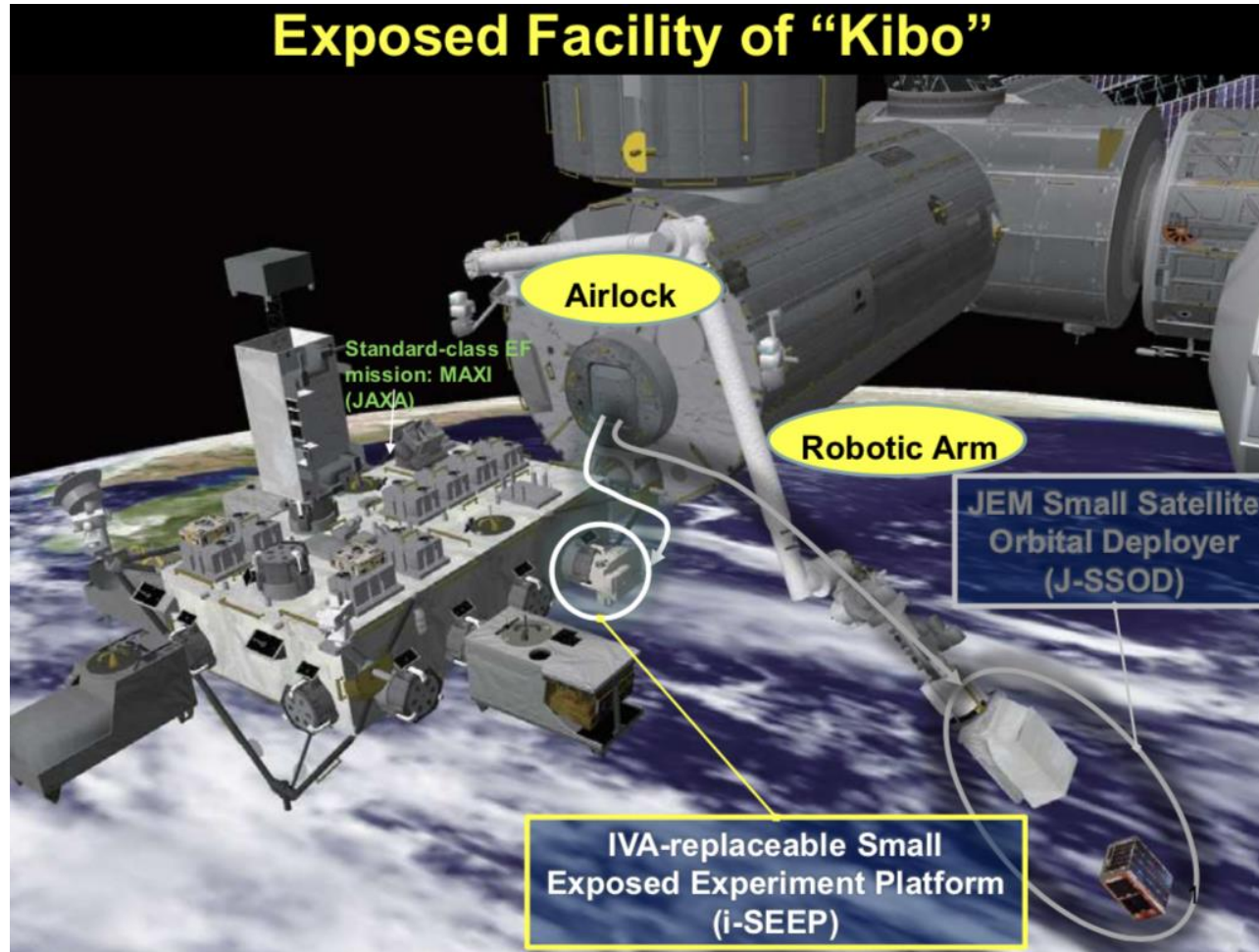
Publication

FAQ





# Testing Platform



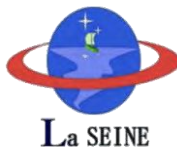
# Mission Statement



To develop and launch a 3U CubeSat, named **SP**Ac**e R**adiation **eX**posure (**SPARX**), and perform the **COTS Irradiated iN** Space (**COINS**) experiment onboard ISS, particularly in-situ measurements of **total ionizing doze** and on-orbit mapping of **single event latchup**, providing a testbed for advanced technology demonstration with a hyperspectral imager and gathering scientific data for 1 year (nominal mission duration).



# Scientific Objectives



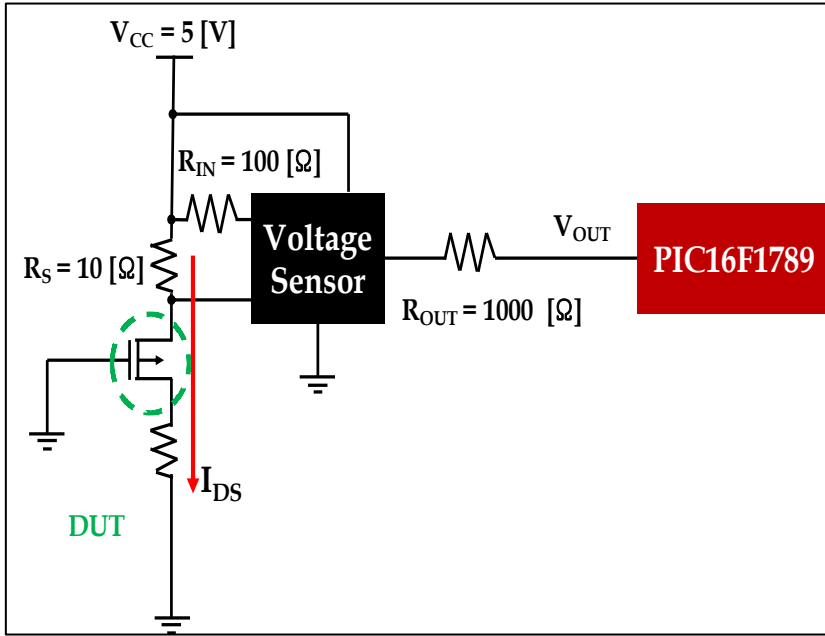
- ❑ To verify the **radiation tolerance** of **power MOSFETs** under **actual space radiation** environment
- ❑ To measure and map **single-event-latchup** in orbit by taking log of **microcontroller reset events** over a period of time
- ❑ To **compare** Earth-based testing techniques such as **Cobalt-60 gamma radiation** and **Californium 252 (Cf 252)** with on-orbit radiation data

# Technological Objective

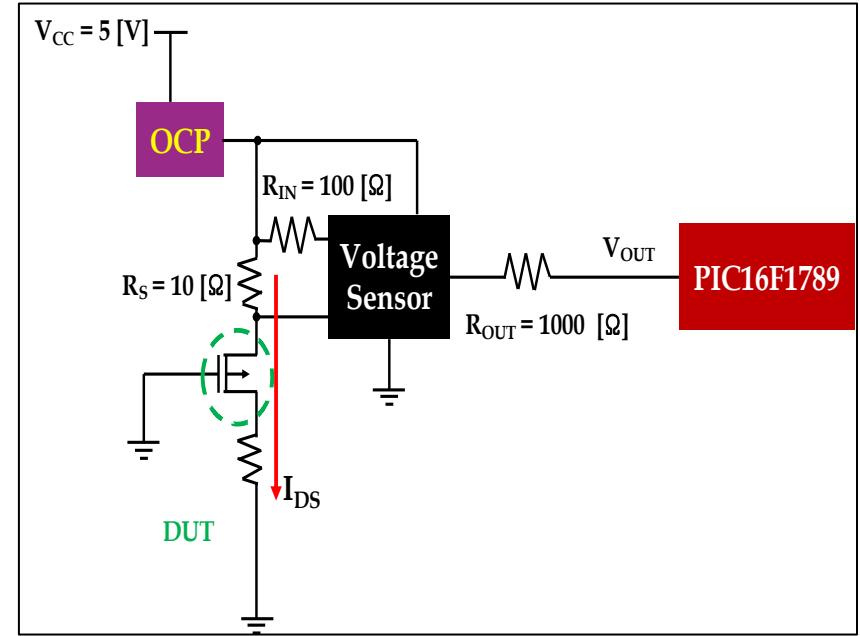


- To demonstrate **hyperspectral imaging** of **tropical cyclones** in the Indian Ocean between Madagascar and the Mozambique channel with a **CubeSat**

# Experimental Concept



Ground-testing setup



Space-testing setup

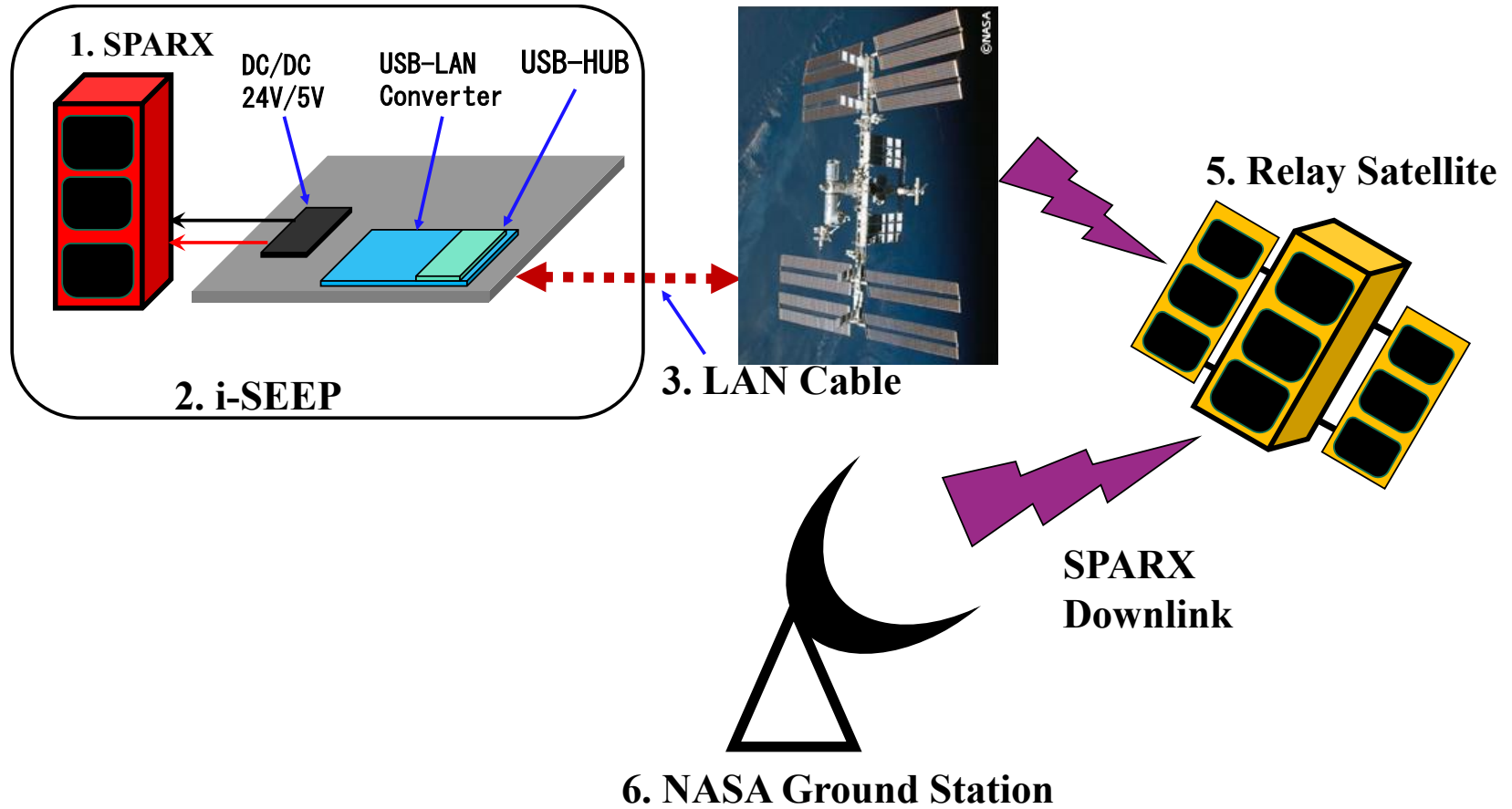
## Functional Requirements

- The mission shall **withstand** deployment forces, vibration, and fluctuating operation temperatures
- The mission shall **survive** a total dose equivalent to 30 krad

## Performance Requirements

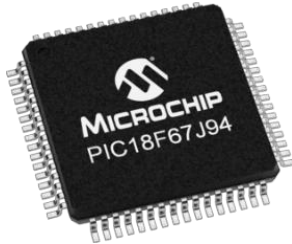
- The **structural frame** shall be **compliant** with 3U CubeSat standards
- **Uninterrupted electrical power** shall be **sourced** from i-SEEP via USB cable and peak power consumption shall not exceed 50 W
- The **on-board computer** shall transfer **scientific data** from **flash memory** to i-SEEP via Ethernet (IEEE 802.11n) and data rate shall not exceed 100 kbps

# Space Segment (1/5)



## Test Articles for Single Events

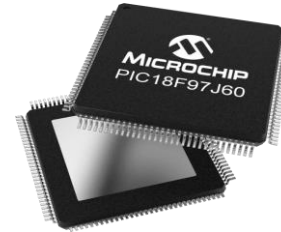
PIC18F67J94



H8



PIC18F97J60



Ground-testing data for most these microcontrollers are currently available

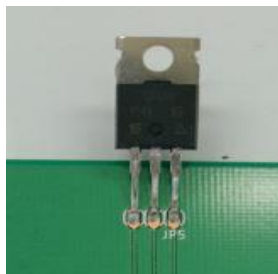


## Test Articles for Ionizing Doze

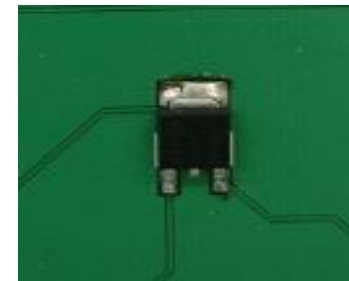
MOSFET	P- Channel IRLML6402	N-Channel IRF620PBF	P-Channel NTD2955
Power consumption	153.0 mW	46.05 mW	49.06 mW
Manufacturer	International Rectifier	Vishay	ON Semiconductor



**Pch**  
**IRLML6402**



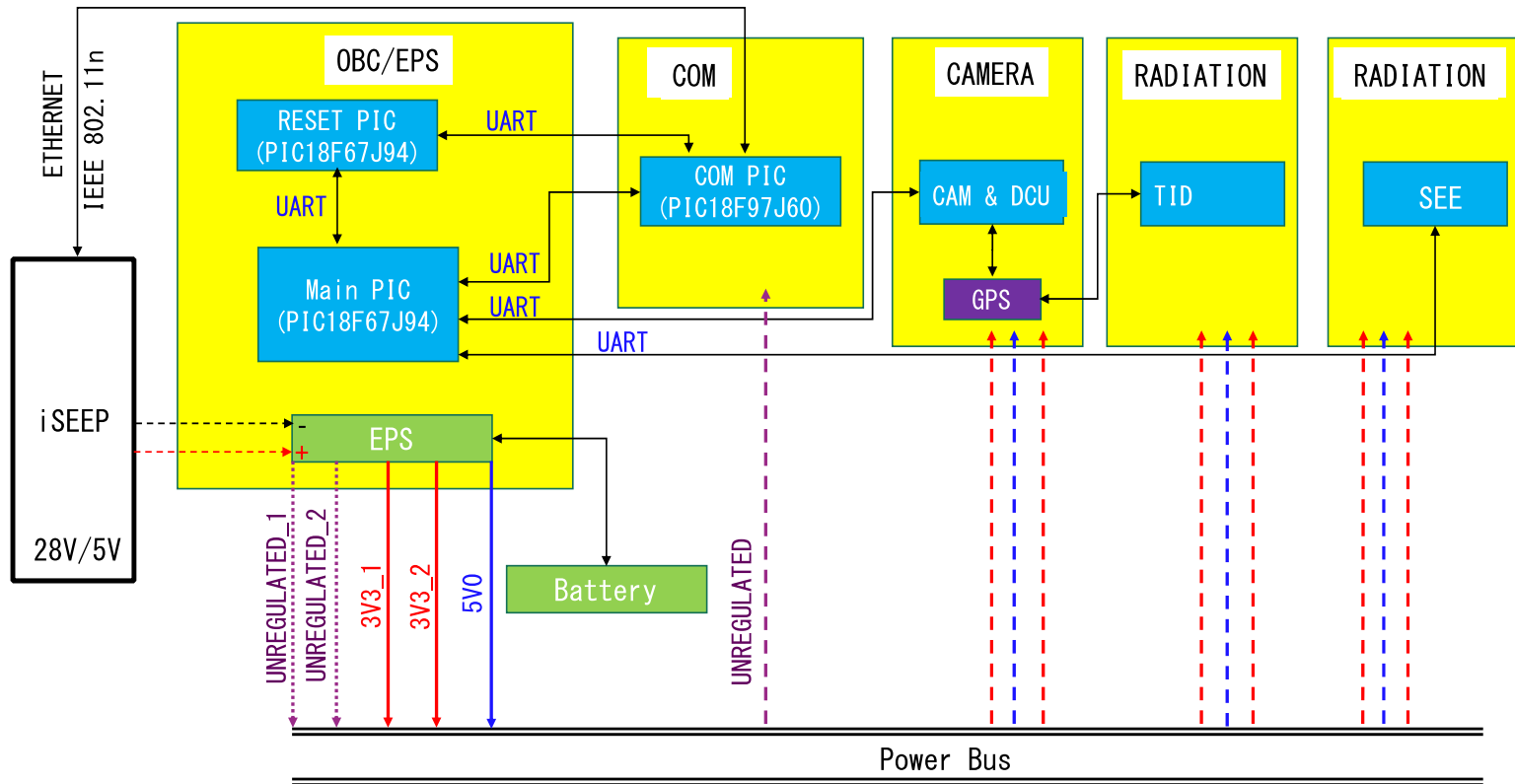
**Nch**  
**IRF620PBF**



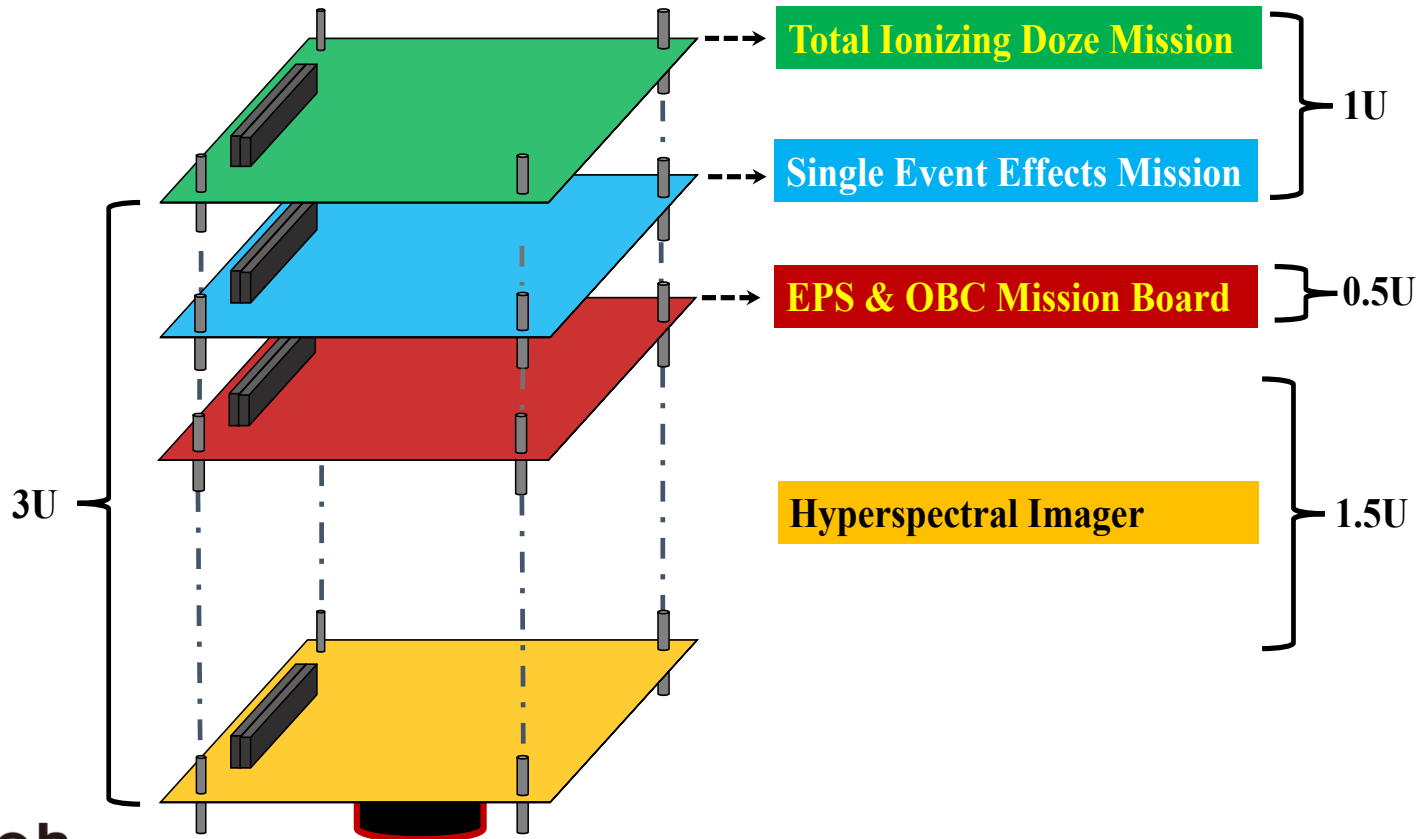
**Pch**  
**NTD2955**

# Space Segment (4/5)

## SPARX's Block Diagram

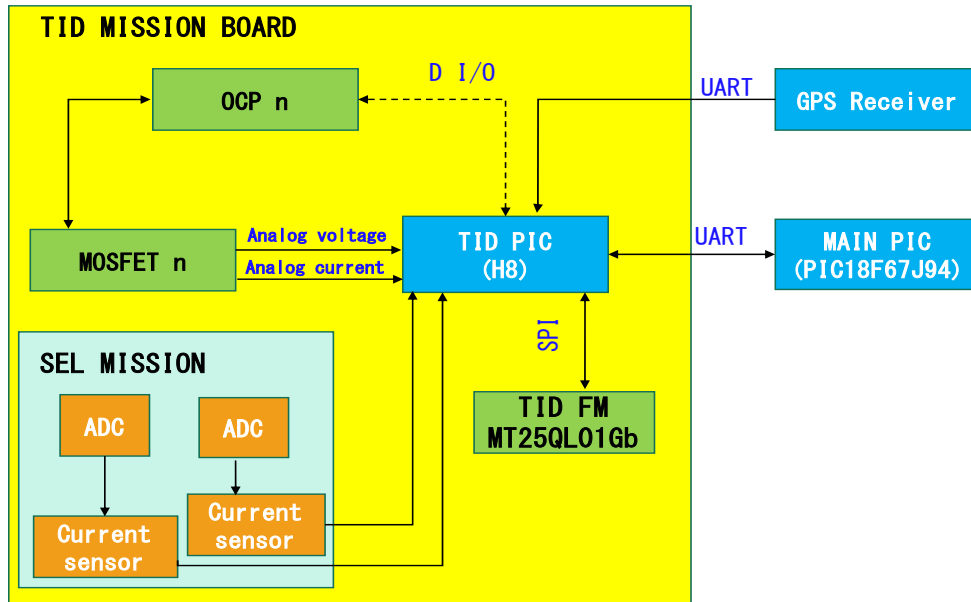


## Mission Boards Sequence



# Concept of Operations (1/2)

## Radiation Mission



- Measure the currents and voltages of power MOSFETs.
- Save science data to local flash memory (TID FM).
- Science data from TID FM is sent to OBC (MAIN PIC)
- MAIN PIC sends science data to PIC18F97J60 microcontroller (IEEE 802.3 compatible)
- PIC18F97J60 transfers science data to iSEEP via Ethernet.

# Concept of Operations (2/2)

## Hyperspectral Imager

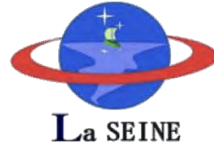
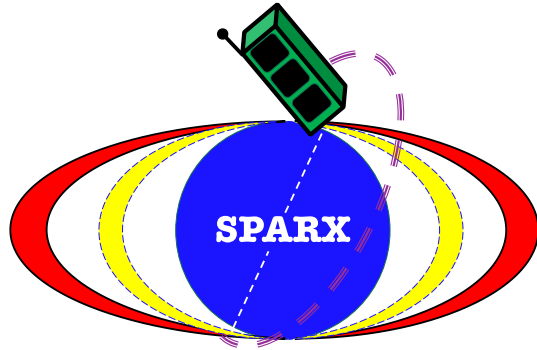
<b>VIS-NIR spectral range</b>	<b>High frame rate RGB Matrix imager or Multispectral line scanning imager or Hyperspectral line scanning imager</b>
<b>Spatial Resolution</b>	<b>9.6m at 500 km</b>
<b>Swath</b>	<b>32 km at 500km</b>
<b>Spectral Bands Multispectral</b>	<b>PAN + up to 10 VIS-NIR bands or RGB Bayer matrix or 150 Hyperspectral bands</b>
<b>Integrated mass storage</b>	<b>160 GB</b>
<b>Power consumption</b>	<b>during readout mode &lt; 2.5W during imaging mode &lt; 3.5W</b>



# Implementation Plan



# Project Costs and Partners



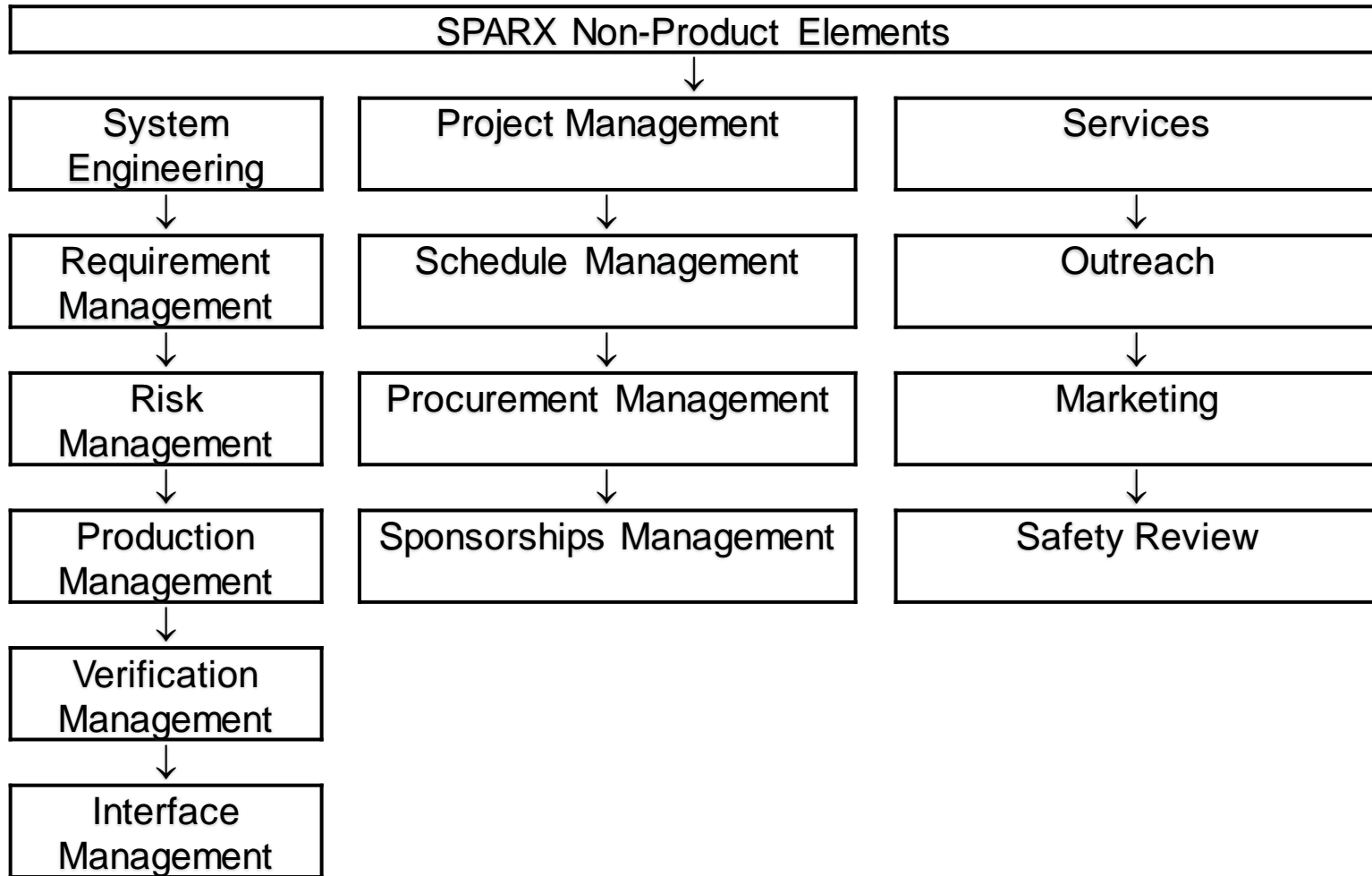
Task /Item	Cost (USD)	Financer
COTS Components + 3U Chassis + PCBs Fabrication Hyperspectral Imager	6700   160,000	National Commission on Research Science and Technology Mozambique National Meteorology Institute + African Union
Environmental Testing H3 Launch Vehicle + i-SEEP Facility + Payload Return +	30,000 419,754.50  	LaSEINE JAXA WMO Crowd Funding
<b>Total</b>	<b>616,454.50</b>	

# Risks and Countermeasures

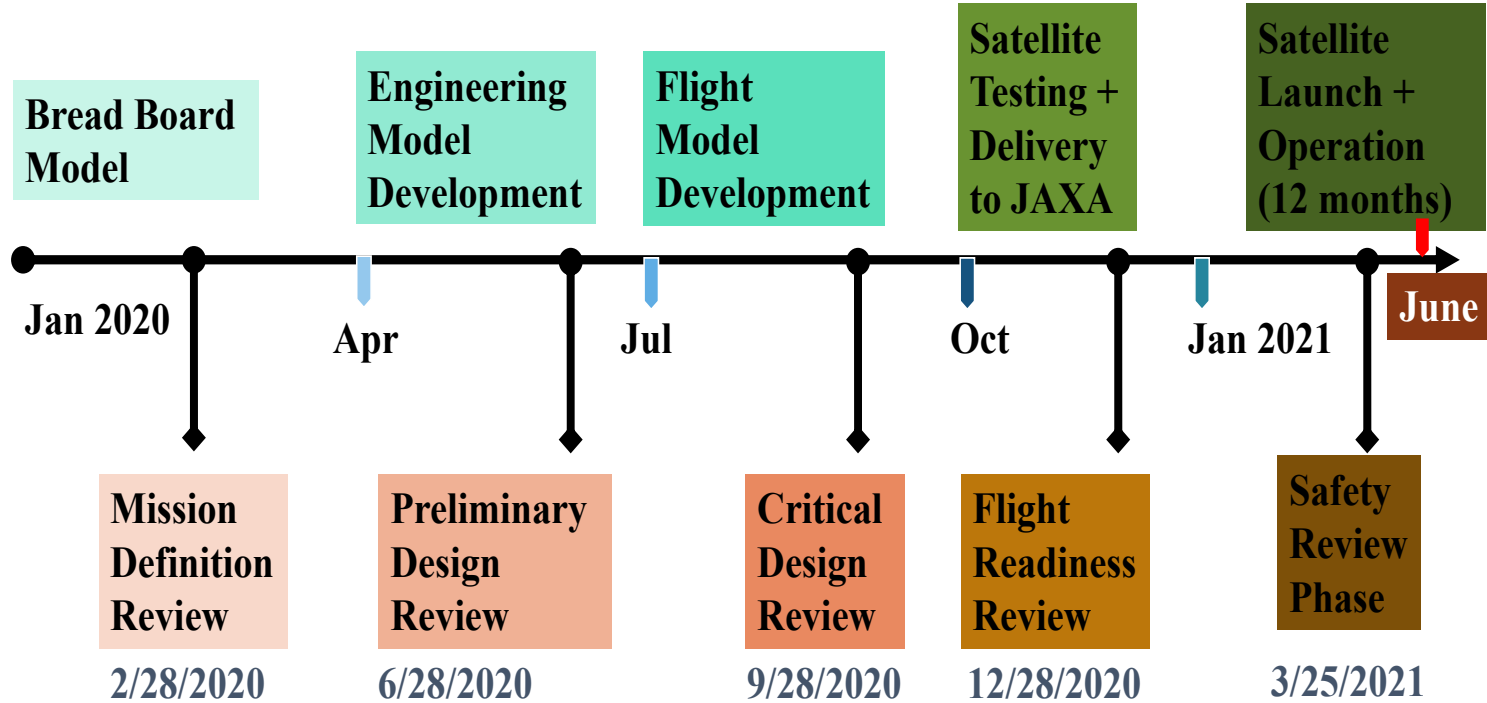


<b>Risk</b>	<b>Probability</b>	<b>Countermeasure</b>
Single Event Upsets	Medium	Error Correction Code (ECC)
Single Event Latchup	Medium	Power Cycling/Periodic Restarts
Flash Memory Failure	High	Redundant Memories
Single Event Burnout	Medium	Shielding
Large Data Rate	High	Onboard Data Compression

# Project Organization



# Project Timeline



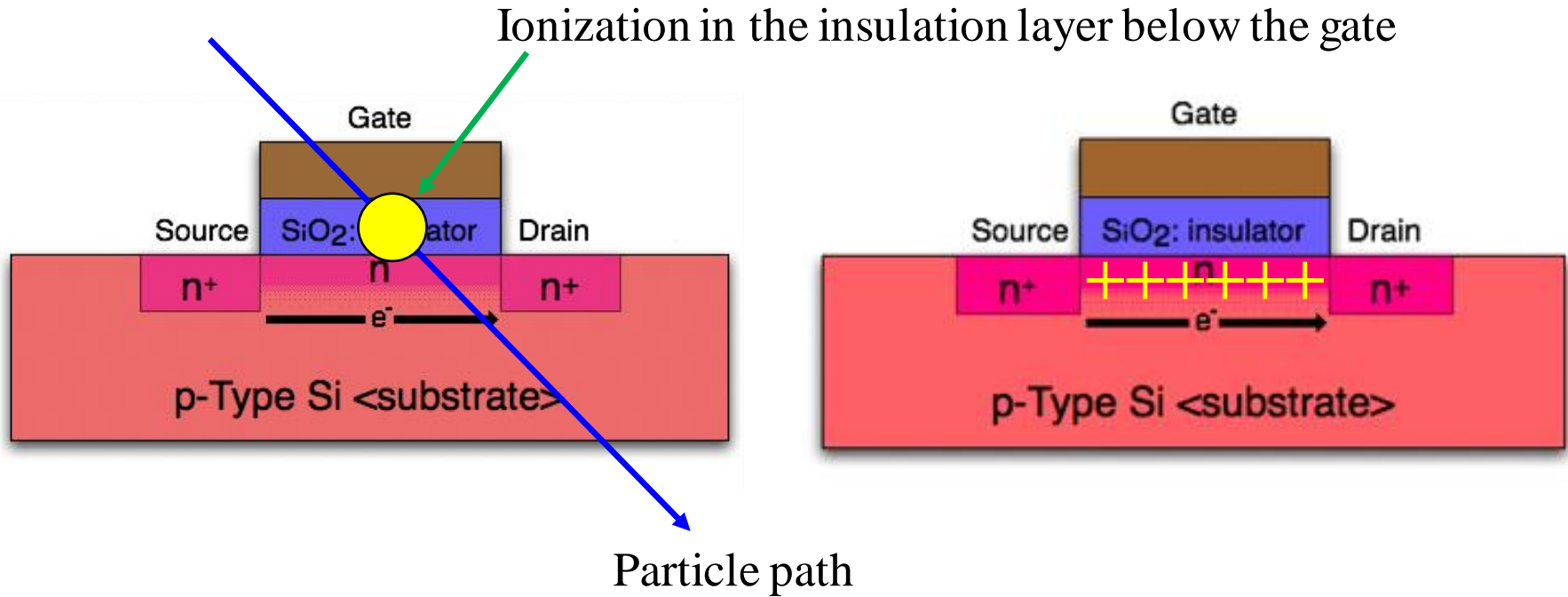
- [1] D. Sinclair and J. Dyer, Radiation effects and COTS parts in SmallSats. *27<sup>th</sup> Annual AIAA/USU Conference on Small Satellites, SSC13-IV-3* (2013)
- [2] S. Kayali, Reliability of Compound Semiconductor Devices for Space Applications, *Microelectronics Reliability 1723-1736* (1999)
- [3] K. A. LaBel *et al.*, Radiation Evaluation Method of Commercial Off-The-Shelf (COTS) electronic Printed Circuit Boards (PCBs), *Fifth European Conference on Radiation and Its Effects on Components and Systems. RADECS 99 (Cat. No.99TH8471)*, Fontevraud, France, 528-534 (1999)
- [4] S. Kayali, Utilization of COTS Electronics in Space Application, Reliability Challenges and Reality (2002)
- [5] J.C. Javier, Radiation testing of COTS electronic parts for lean satellite. Master Thesis, Kyushu Institute of Technology (2018)
- [6] BIRDS Project Newsletter – No .44. Available online at: <http://birds1.birds-project.com/newsletter.html> (accessed October 2019)
- [7] R. Ecoffet, Spacecraft Anomalies Associated with Radiation Effects. *RADECS 2013 Short Course Proceedings, Chap. VIII* (2013)
- [8] M. Cho, Radiation. Available online at: [https://kyutech-laplace.net/Class/2019/Class\\_SET/Materials/2019\\_Space\\_env\\_test\\_6\\_radiation\\_v5.pdf](https://kyutech-laplace.net/Class/2019/Class_SET/Materials/2019_Space_env_test_6_radiation_v5.pdf) (accessed September 2019)
- [9] T. Murase, Improvement of the value of commercial components by improving radiation test. Kyushu Institute of Technology (2019)
- [10] Solar Cycle 25 Preliminary Forecast. Available online at: <https://www.weather.gov/news/190504-sun-activity-in-solar-cycle> (accessed October 2019)
- [11] V. Gupta. Analysis of single event radiation effects and fault mechanisms in SRAM, FRAM and NAND Flash: application to the MTCube nanosatellite project. *Electronics*. Université Montpellier (2017)
- [12] 2019 Cyclone Idai: Facts, FAQs, and how to help. Available online at: <https://www.worldvision.org/disaster-relief-news-stories/2019-cyclone-idai-facts> (accessed October 2019)
- [13] Chameleon Imager. Available online at: <https://www.cubesatshop.com/product/chameleon-imager/> (accessed October 2019)





# Introduction (4/5)

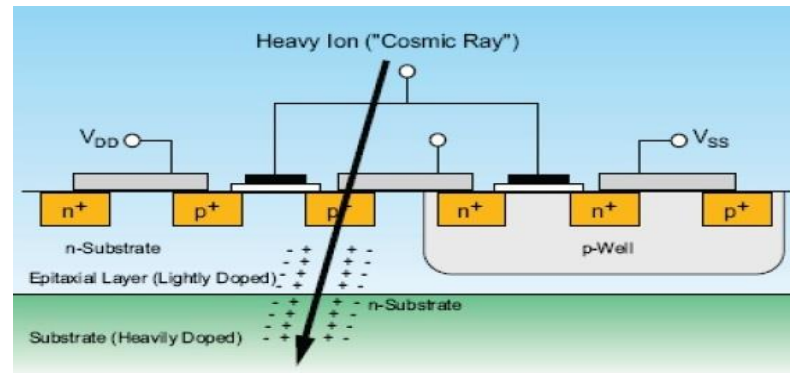
## Total Ionizing Doze



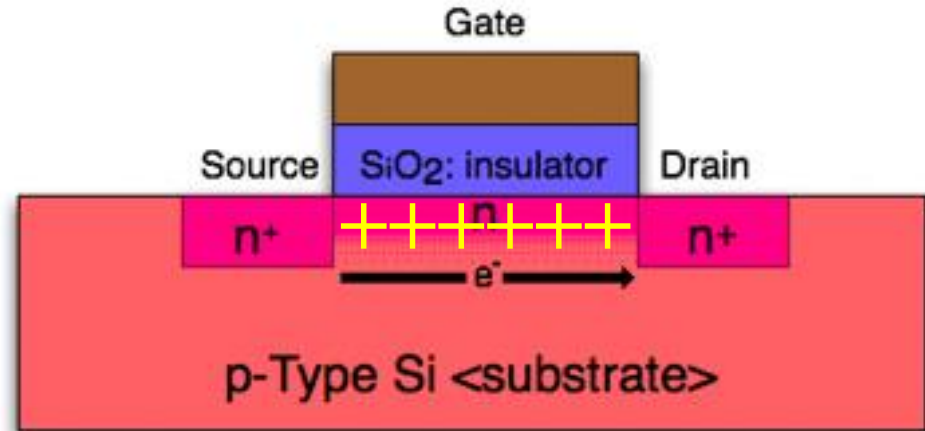
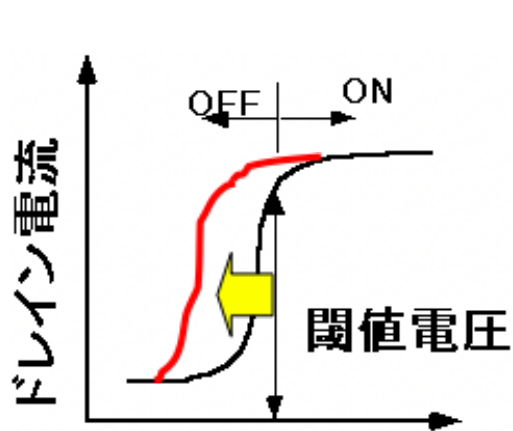
# Introduction (4/5)

## Single Event Latchup (SEL)

- An **abnormal high-current** state in a device caused by the passage of a single energetic particle through sensitive regions of the device structure and resulting in the loss of device functionality



# Introduction (5/5)



## ゲート電圧 MOS-FETの動作特性

- The gate needs less voltage to turn on the switch by the positive voltage produced by the remaining positive charge
- Decrease of the threshold voltage
- Change of MOS operational points
- The effect disappears as the holes move away from the insulation layer
- – Takes a long time( $>10^8$  sec)

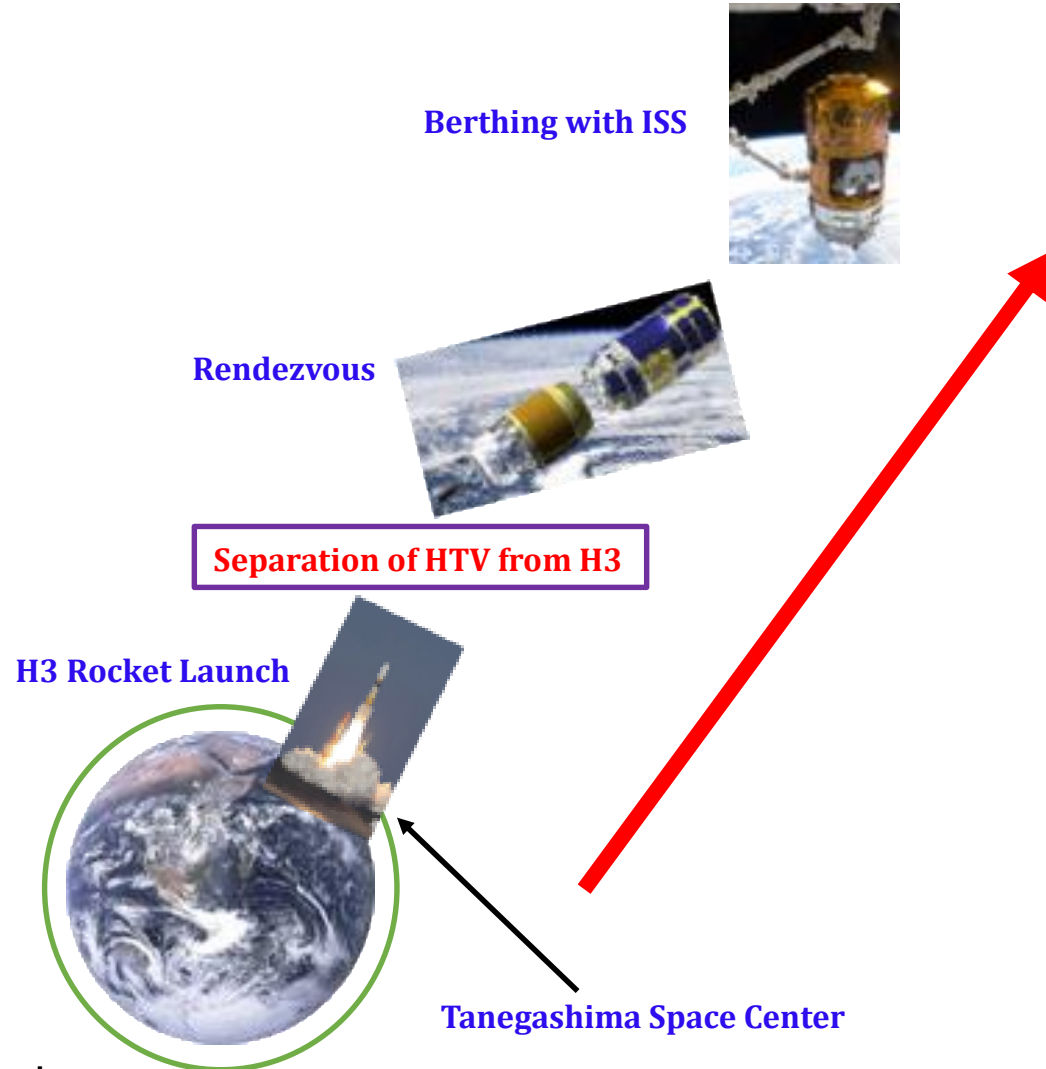
# Single Event Effects (SEE)

- Disruption in function of electronic circuits due to single ionizing particle interaction.
  - **Single Event Upset (SEU)** – bit flips
  - **Single Event Latchup (SEL)** – parasitic
  - **Single Event Functional Interrupt (SEFI)**
    - Soft error, can be recoverable without power reset, unlike SEL
  - **Single Event Burnout (SEB)**
    - Current induced by heavy ion penetration destroys Power MOSFET
  - **Single Event Gate Rupture (SEGR)**
    - Failure of oxide layer of Power MOSFET by current

*Doug Sinclair and Jonathan Dyer, “Radiation Effects and COTS Parts in SmallSats”,  
Small Satellite Conference, 2013*

- **Particles or electromagnetic wave** with energy high enough to affect chemical or nuclear properties of material.
- **Charged particles**
  - Electron
  - Proton
  - Alpha particle (nucleus of Helium)
  - Heavy ions
- **Particle**
  - Neutron
- **Electromagnetic wave (photon)**
  - Gamma ray, typically less than 10-12m ( $>1\text{MeV}$ )
    - – Originate from nuclear interactions
  - X ray, typically 10-11 ~ 10-8 m (100~100keV)
    - Originate from collisions of charged particles
  - UV ray, typically 10nm ~ 380nm (3eV~100keV)

# Launch & Rendezvous to ISS



<b>Radiation Effect</b>	<b>Total Ionizing Doze (TID)</b>	<b>Single Event Effects (SEE)</b>	<b>Displacement Damage</b>
<b>Definition</b>	Material damage caused by ionizing radiation sources. Qualified by deposited energy per mass for a given material with units of Gray (SI) or Rad [1].	Disruption in function of electronic circuits due to single ionizing particle interaction [1].	Change of semiconductor properties such as carrier lifetime due to protons and energetic electrons.
<b>Degree of impact</b>	Cumulative (Semi-infinite)	Abrupt (Transient)	Cumulative (Non-reversal)